



Description

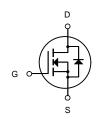
The DMTH4014LPSW-13 uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

DFN5X6-8L

General Features

 $V_{DS} = 40V I_{D} = 40A$

 $R_{DS(ON)} < 14m\Omega$ $V_{GS}=10V$



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMTH4014LPSW-13	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings (Tc=25 ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units		
V _{DS}	Drain-Source Voltage	n-Source Voltage 40			
Vgs	Gate-Source Voltage	±20	V		
Io@Tc=25°C	Continuous Drain Current, V _{GS} @ 10V ¹	40	Α		
I _D @T _C =100°C	Continuous Drain Current, Vos @ 10V1	28	Α		
Ірм	Pulsed Drain Current ²	160	Α		
EAS	Single Pulse Avalanche Energy ³	50	mJ		
Тѕтс	Storage Temperature Range	Storage Temperature Range -55 to 175			
TJ	Operating Junction Temperature Range	-55 to 175	°C		



Electrical Characteristics (T_C=25 ℃ unless otherwise noted)

Parameter	Symbol	bol Condition		Тур	Max	Unit	
Off Characteristics	·						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA 40		-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1	1.6	2.5	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	11	14	mΩ	
Forward Transconductance	g fs	V _{DS} =5V,I _D =20A	30	-	-	S	
Dynamic Characteristics (Note4)	·		•				
Input Capacitance	C _{lss})/ 05)/)/ 0)/	-	1540	-	PF	
Output Capacitance	Coss	V_{DS} =25 V , V_{GS} =0 V , F=1.0MHz	-	171	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.UIVITIZ	-	115	-	PF	
Switching Characteristics (Note 4)			'				
Turn-on Delay Time	t _{d(on)}		-	5.0	-	nS	
Turn-on Rise Time	t _r	V_{DD} =20V, I_D =20A, R_E =1 Ω	-	24	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =3 Ω	-	38	-	nS	
Turn-Off Fall Time	t _f		-	12	-	nS	
Total Gate Charge	Qg	V -20VI -20A	-	24	-	nC	
Gate-Source Charge	Q_{gs}	V _{DS} =30V,I _D =30A, V _{GS} =10V	-	5.9	-	nC	
Gate-Drain Charge	Q_{gd}	V _{GS} -10V	-	3.6	-	nC	
Drain-Source Diode Characteristics	·						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =30A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	40	Α	
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =30A	-	9		nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	15		nC	
Forward Turn-On Time	rd Turn-On Time t _{on} Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)						

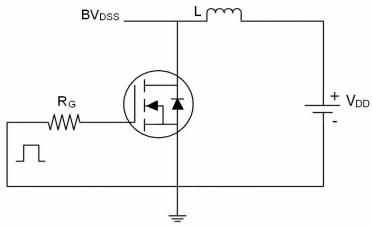
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition: Tj=25 $^{\circ}$ C,V_{DD}=30V,V_G=10V,L=0.5mH,Rg=25 Ω

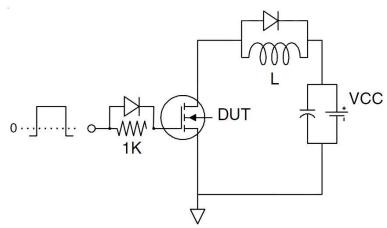


Test circuit

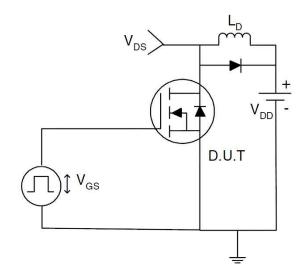
1) E_{AS} test Circuits



2) Gate charge test Circuit

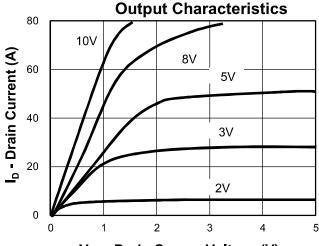


3) Switch Time Test Circuit

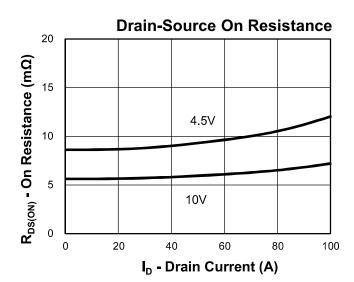


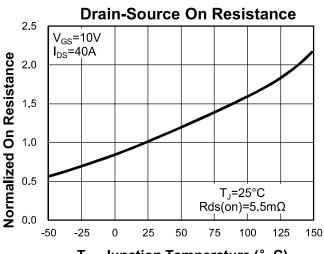


Typical Performance Characteristics

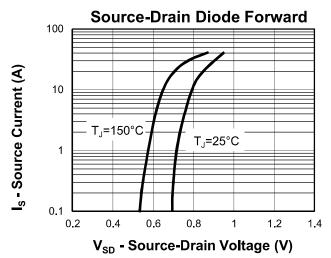




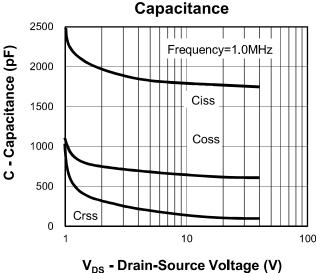


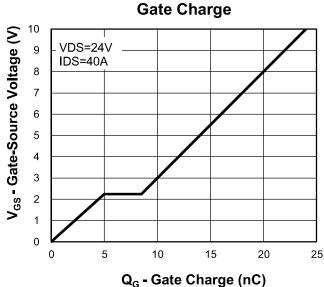


T_{.1} - Junction Temperature (° C)

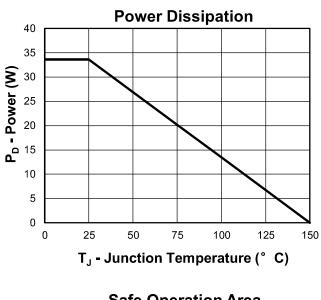


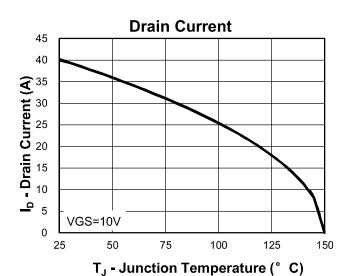


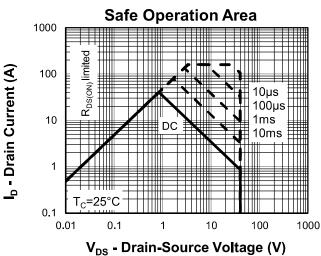


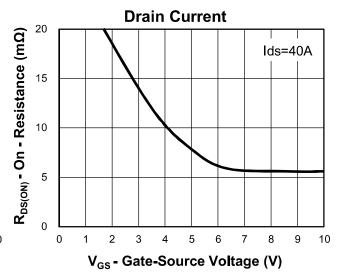




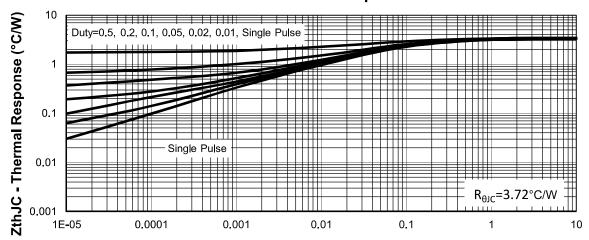








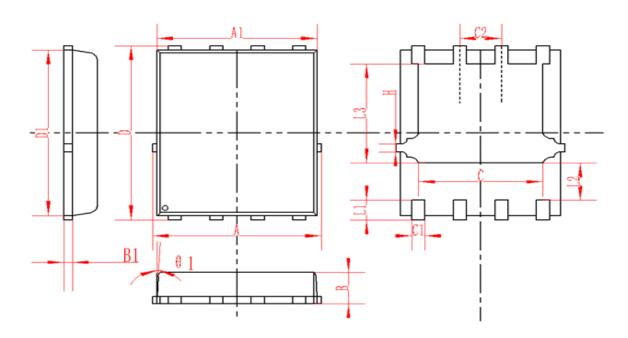
Thermal Transient Impedance



Square Wave Pulse Duration (sec)



DFN5X6-8L Package Information



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1		0.254REF			0.010REF	
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



N-Channel Enhancement Mode MOSFET

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